

d hist

(FILE 'USPAT' ENTERED AT 15:07:45 ON 03 MAR 93)

L1 192227 S SEMICONDUCT? OR SILICON OR SI
L2 13302 S (IMPURITIES OR IMPURITY) AND CARBON AND NITROGEN AND OXY
GEN
L3 5268 S L1 AND L2
L4 1467 S L3 AND AMORPHOUS
L5 125 S L4 AND RECRYSTAL?
L6 0 S L5 AND CCLS/257
L7 0 S 257/CCLR
L8 9 S L5 AND (THIN FILM)

=>

d 18 1-9

1. 5,157,027, Oct. 20, 1992, Bisphosphonate squalene synthetase inhibitors and method; Scott A. Biller, et al., 514/107, 105, 108; 549/220, 221, 222; 558/77, 83, 155, 161; 562/21 [IMAGE AVAILABLE]
2. 5,123,975, Jun. 23, 1992, Single crystal silicon substrate; Mitsugu Irinoda, et al., 148/33.2, 33.3; 156/603, 604; 437/46, 62, 83, 84, 174, 233, 973 [IMAGE AVAILABLE]
3. 5,117,057, May 26, 1992, Insecticidal N' substituted-N-N'-disubstituted-hydrazines; Adam C. Hsu, et al., 564/149; 544/224, 335, 406; 546/316, 324, 325, 332; 548/213, 214, 238, 248, 255, 537, 563; 549/65, 72, 436, 484, 487, 494, 496, 553; 556/419; 558/6, 10, 17, 58, 273, 275, 404, 415; 560/27, 29, 30, 34, 138, 163, 221, 251; 564/12, 35, 36, 74, 81, 148, 150, 151 [IMAGE AVAILABLE]
4. 5,108,843, Apr. 28, 1992, Thin film semiconductor and process for producing the same; Kouichi Ohtaka, et al., 428/446, 212, 428, 698; 699, 701, 704 [IMAGE AVAILABLE] CM1-8C14
5. 5,006,395, Apr. 9, 1991, Iron carbide thin film magnetic recording medium; Toshiro Hori, et al., 428/141; 427/127, 131; 428/688, 694, 900 [IMAGE AVAILABLE]
6. 4,916,470, Apr. 10, 1990, Image bar with electrochromic switching system; Gregory J. Kovacs, et al., 346/160, 155 [IMAGE AVAILABLE]
7. 4,772,678, Sep. 20, 1988, Liquid crystalline polymer compositions, process, and products; Joanne R. Sybert, et al., 528/179; 524/417; 528/183, 188, 327, 330, 331, 337, 341, 342, 346, 347, 348, 352, 353, 364
8. 4,727,044, Feb. 23, 1988, Method of making a thin film transistor with laser recrystallized source and drain; Shunpei Yamazaki, 437/45; 257/52, 347; 437/46, 82, 83, 100, 101, 907 CP3 loc24
9. 4,668,331, May 26, 1987, Method for forming single crystals of silicon by use of a standing hypersonic wave; Jeremiah P. Ostriker, 156/603; 148/DIG.98; 156/620.71, DIG.91 10D17 437

=> d 15 51 61 66

51. 4,814,292, Mar. 21, 1989, Process of fabricating a semiconductor device involving densification and recrystallization of amorphous silicon; Masayoshi Sasaki, et al., 437/101; 148/DIG.1; 437/40, 83, 84, 233, 247, 248

61. 4,727,044, Feb. 23, 1988, Method of making a thin film transistor

257/52, 347; 437/46, 82, 83, 100, 101, 907

66. 4,668,331, May 26, 1987, Method for forming single crystals of
~~silicon~~ by use of a standing hypersonic wave; Jeremiah P. Ostriker,
156/603; 148/DIG.98; 156/620.71, DIG.91

=> d 15 kwic 51 61 66

US PAT NO: 4,814,292
TITLE: Process of fabricating a semiconductor device

L5: 51 of 125

Raman 5036,373 257/86,77,103